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MICR131.0

09/503,638

Kirk D. Prall

Filing Date

2/14/00

Group Art Unit

U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

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EXAMINER

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Serial No. 09/503,638

COPIES OF THE CITED REFERENCES ON THE ATTACHED INFORMATION
DISCLOSURE CITATION WERE PREVIOUSLY CITED BY OR SUBMITTED TO
THE PATENT OFFICE IN THE PARENT APPLICATION, WHICH IS U.S.
PATENT APPLICATION SERIAL NO. 08/868,058 FILED JUNE 3, 1997,
WHICH IS A DIVISIONAL OF U.S. PATENT APPLICATION SERIAL NO.
08/399,843 FILED MARCH 7, 1995.

INFORMATION DISCLOSURE CITATION

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Docket Number (Optional)

MICR131

Application Number

Applicant(s)

Kirk D. Prall, et al.

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09/503638

02/14/00

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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JP		Hurkx et al., A New Recombination Model for Device Simulation Including Tunneling, IEEE TRED Vol. 39, No. 2 Feb. 1992, pages 331-338.
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EXAMINER	DATE CONSIDERED 8/24/01	

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Kirk D. Prall et al.

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Group Art Unit

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EXAMINER

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